

### Peak Emission Wavelength: 870nm

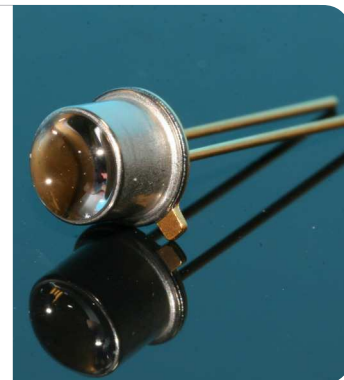
The 870nm high power infrared emitter series is designed for application requiring high accuracy and precision as well as uniform spectral emission. Custom package solutions and sorting are available.

#### FEATURES

- > Hermetically Sealed TO-46
- > High Output Power
- > High Reliability
- > Narrow Beam Angle

#### APPLICATIONS

- > Optical Scanning
- > Linear & Rotary Encoder
- > Edge Sensing / Optical Sensors
- > Optical Switches / Security Systems



### Absolute Maximum Ratings (Ta=25°C)

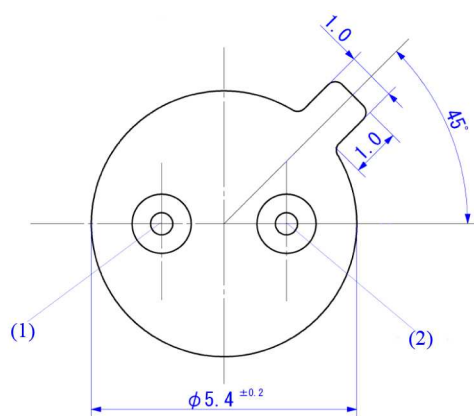
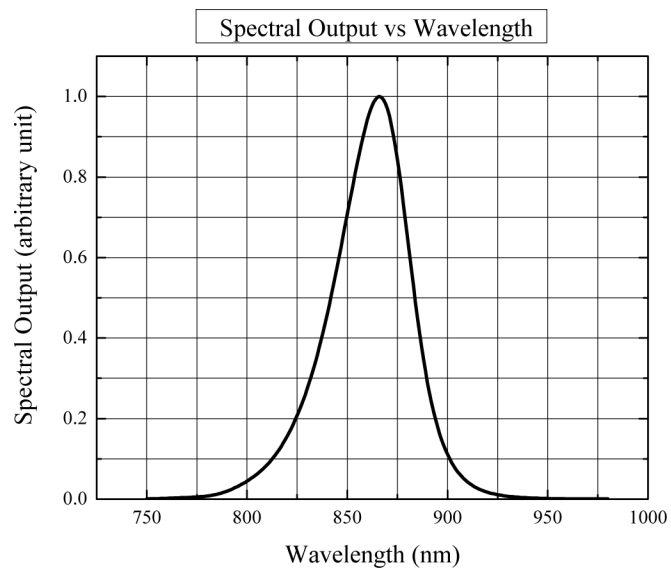
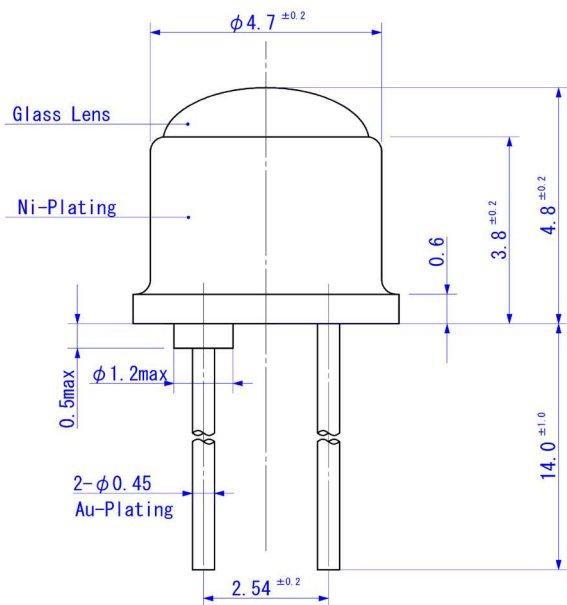


ITEMS	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	100	mA
Forward Current (Pulse)*1	IFP	1	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	200	mW
Operating Temperature Range	Topr	-30 ~ +100	°C
Storage Temperature Range	Tstg	-40 ~ +125	°C
Junction Temperature	Tj	125	°C
Lead Soldering Temperature*2	Tls	260	°C

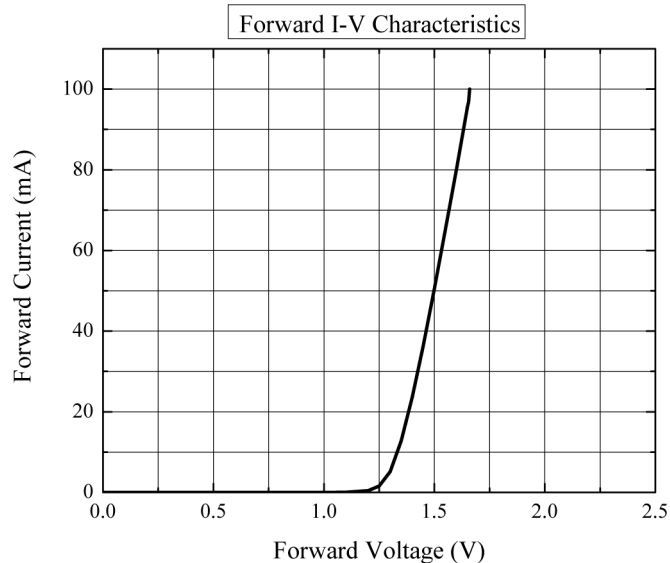
\*1: Tw=10μsec, T=10msec. \*2: Time 5 Sec max, Position: Up to 3mm from the body.

### Electrical & Optical Characteristics (Ta = 25°C)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA	--	10.0	--	mW
Forward Voltage	VF	IF=50mA	--	1.5	2.0	V
Reverse Current	IR	VR=5V	--	--	10	μA
Peak Emission Wavelength	λp	IF=50mA	--	870	--	nm
Spectral Line Half Width	Δλ	IF=50mA	--	45	--	nm
Half Intensity Beam Angle	Θ	IF=50mA	--	±4	--	deg



- ①. Cathode
- ②. Anode



Unit: mm, Tolerance:  $\pm 0.2$

Relative Power Output vs. Forward Current

